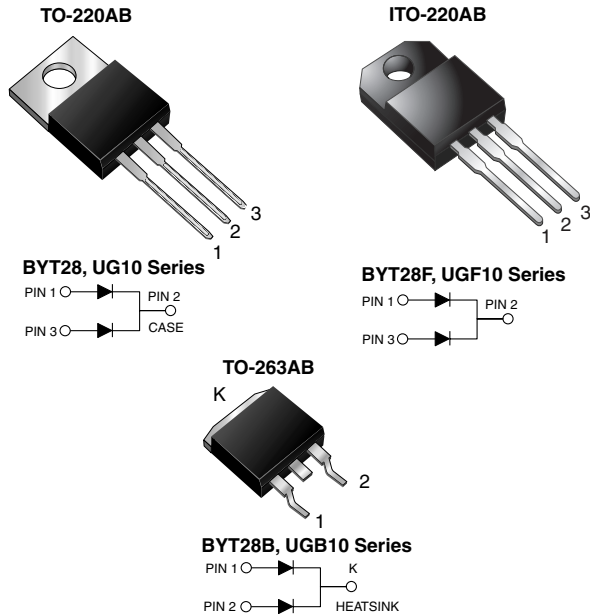




Dual Common-Cathode Ultrafast Soft Recovery Rectifier



FEATURES

- Glass passivated chip junction
- Ultrafast recovery time
- Low switching losses, high efficiency
- Low forward voltage drop
- High forward surge capability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder dip 260 °C, 40 s (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

RoHS
COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency rectifier of switching mode power supplies, inverters, freewheeling diodes, dc-to-dc converters, and other power switching application.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	5 A x 2
V_{RRM}	300 V, 400 V
I_{FSM}	60 A
t_{rr}	35 ns
V_F	1.05 V
$T_J \text{ max.}$	150 °C

MAXIMUM RATINGS ($T_C = 25 \text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	BYT28-300 UG10FCT	BYT28-400 UG10GCT	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	300	400	V
Maximum working reverse voltage	V_{RWM}	300	400	V
Maximum RMS voltage	V_{RMS}	210	280	
Maximum DC blocking voltage	V_{DC}	300	400	V
Maximum average forward rectified current at $T_C = 100 \text{ °C}$ total device per diode	$I_{F(AV)}$	10 5.0		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	60		A
Operating junction and storage temperature range	T_J, T_{STG}	- 40 to + 150		°C
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1 \text{ min}$	V_{AC}	1500		V

ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)					
PARAMETER	TEST CONDITIONS		SYMBOL	VALUE	UNIT
Maximum instantaneous forward voltage per diode ⁽¹⁾	$I_F = 5\text{ A}$, $I_F = 10\text{ A}$ $I_F = 5\text{ A}$	$T_J = 25\text{ }^{\circ}\text{C}$ $T_J = 25\text{ }^{\circ}\text{C}$ $T_J = 150\text{ }^{\circ}\text{C}$	V_F	1.30 1.40 1.05	V
Maximum reverse current per diode at V_{RRM}		$T_J = 25\text{ }^{\circ}\text{C}$ $T_J = 100\text{ }^{\circ}\text{C}$	I_R	10 200	μA
Maximum reverse recovery time per diode	$I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{rr} = 0.25\text{ A}$		t_{rr}	35	ns
Maximum reverse recovery time per diode	$I_F = 1.0\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$, $I_{rr} = 0.1\text{ }I_{RM}$		t_{rr}	50	ns
Maximum reverse recovery current per diode	$I_F = 5\text{ A}$, $dI/dt = 50\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$, $T_C = 100\text{ }^{\circ}\text{C}$		I_{RM}	3.0	A
Maximum stored charge per diode	$I_F = 2\text{ A}$, $dI/dt = 20\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$, $I_{rr} = 0.1\text{ }I_{RM}$		Q_{rr}	50	nC

Note:(1) Pulse test: 300 μs pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS ($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	BYT28 UG10	BYT28F UGF10	BYT28B UGB10	UNIT
Typical thermal resistance junction to case per diode	$R_{\theta JC}$	4.5	6.7	4.5	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	BYT28-400-E3/45	1.80	45	50/tube	Tube
ITO-220AB	BYT28F-400-E3/45	1.95	45	50/tube	Tube
TO-263AB	BYT28B-400-E3/45	1.77	45	50/tube	Tube
TO-263AB	BYT28B-400-E3/81	1.77	81	800/reel	Tape and reel
TO-220AB	BYT28-400HE3/45 ⁽¹⁾	1.80	45	50/tube	Tube
ITO-220AB	BYT28F-400HE3/45 ⁽¹⁾	1.95	45	50/tube	Tube
TO-263AB	BYT28B-400HE3/45 ⁽¹⁾	1.77	45	50/tube	Tube
TO-263AB	BYT28B-400HE3/81 ⁽¹⁾	1.77	81	800/reel	Tape and reel

Note:

(1) Automotive grade AEC Q101 qualified



RATINGS AND CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

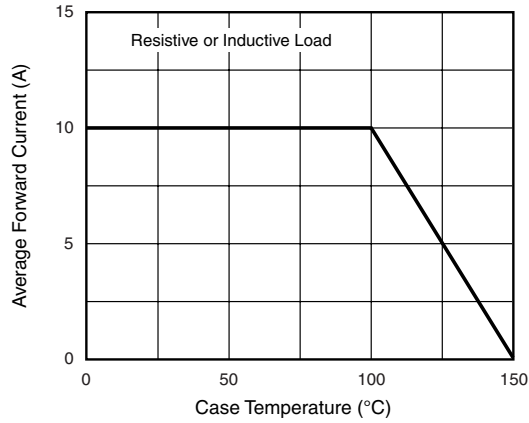


Figure 1. Forward Current Derating Curve

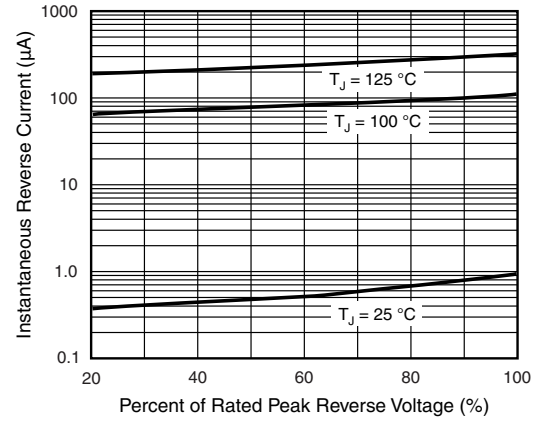


Figure 4. Typical Reverse Characteristics Per Diode

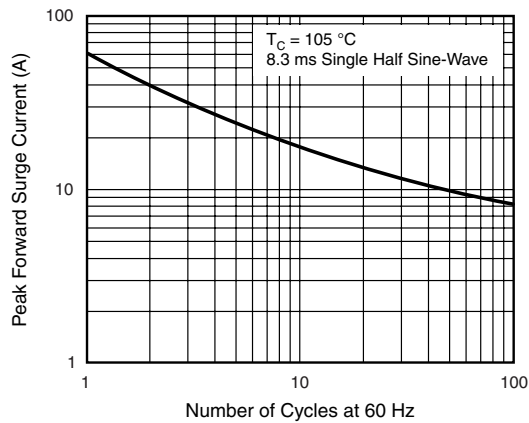


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

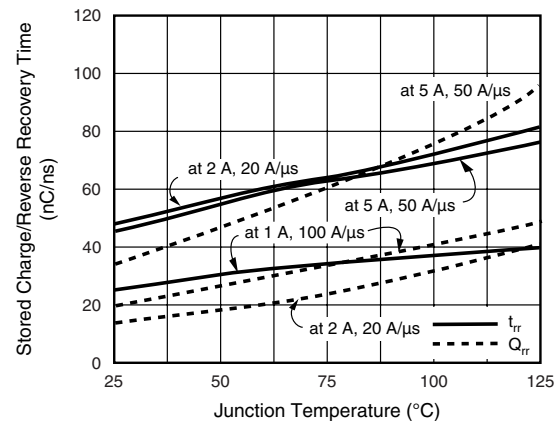


Figure 5. Reverse Switching Characteristics Per Diode

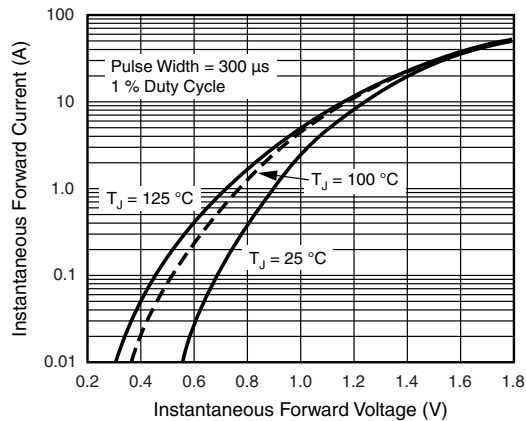


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

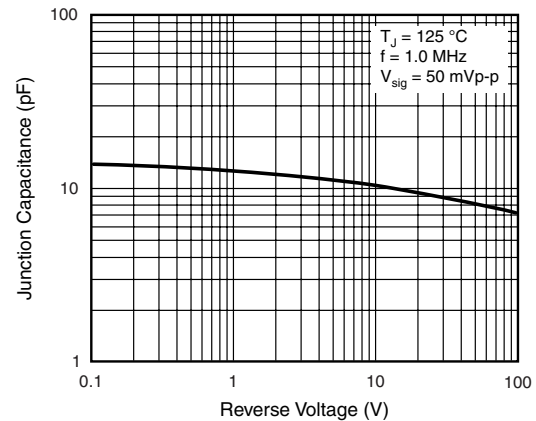


Figure 6. Typical Junction Capacitance Per Diode



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